

Nano-Current Consumed, IoSmart[™] Load Switch

Product Specification

DESCRIPTION

The GLF71511 is an ultra-efficiency, 2 A rated, Load Switch with integrated slew rate control. The best in class efficiency makes it an ideal chose for use in IoT, mobile, and wearable electronics.

The GLF71511 features ultra-efficient I_QSmart^{TM} technology that supports the lowest quiescent current (I_Q) and shutdown current (I_{SD}) in the industry. Low I_Q and I_{SD} solutions help designers to reduce parasitic leakage current, improve system efficiency, and increase battery lifetime.

The GLF71511 integrated slew rate control can also enhance system reliability by mitigating bus voltage swings during switching events. Where uncontrolled switches can generate high inrush currents that result in voltage droop and/or bus reset events, the GLF slew rate control specifically limits inrush currents during turn-on to minimize voltage droop.

GLF71511 Load Switch devices support an industry leading wide input voltage range and helps to improve operating life and system robustness. Furthermore, one device can be used in multiple voltage rail applications which helps to simplify inventory management and reduce operating cost.

GLF71511 Load Switch device is small utilizing a chip scale package with 4 bumps in a 0.97 mm x 0.97 mm x0.55 mm die size and a 0.5 mm bump pitch.

FEATURES

 Wide Operating Temperature Range: -40°C ~ 105°C

Ultra-Low I_Q: 5 nA Typ @ 3.3 V_{IN}
 Ultra-Low I_{SD}: 9 nA Typ @ 3.3 V_{IN}
 Low R_{ON}: 30 mΩ Typ @ 3.3V_{IN}

• Ι_{ΟυΤ} Max: 2 A

Wide Input Range: 1.1 V to 5.5 V
 6 V abs max

Controlled Rise Time: 2.2 ms at 3.3 V_{IN}

Internal EN Pull-Down Resistor

Integrated Output Discharge Switch

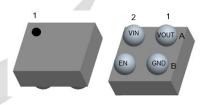
• HBM: 6 kV, CDM: 2 kV

 Ultra-Small: 0.97 mm x 0.97 mm x 0.55 mm WLCSP 4 Bumps, 0.5 mm Pitch

APPLICATIONS

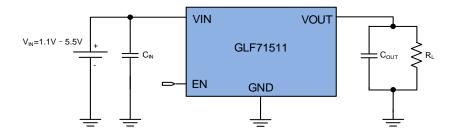
- Telecommunication Module
- Data Storage
- Mobile Devices
- Low Power Subsystems

PACKAGE



0.97 mm x 0.97 mm x 0.55 mm WLCSP

APPLICATION DIAGRAM



ALTERNATE DEVICE OPTIONS

Part Number	Top Mark	R _{ON} (Typ) at 3.3V	Output Discharge	EN Activity
GLF71511	CD	30 mΩ	85 Ω	High

FUNCTIONAL BLOCK DIAGRAM

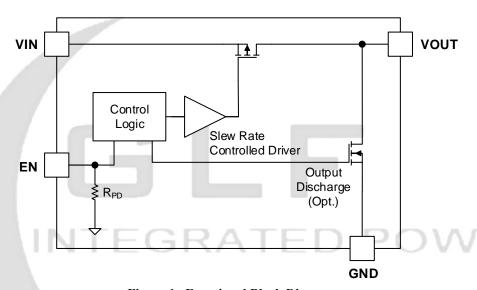


Figure 1. Functional Block Diagram

PIN CONFIGURATION

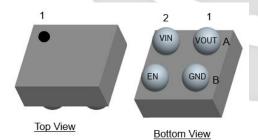


Figure 2. 0.97mm x 0.97mm x 0.55mm WLCSP

PIN DEFINITION

Pin#	Name	Description
A1	Vouт	Switch Output
A2	Vin	Switch Input. Supply Voltage for IC
B1	GND	Ground
B2	EN	Enable to control the switch

ABSOLUTE MAXIMUM RATINGS

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions; extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Par	Min.	Max.	Unit	
Vin	VIN, VOUT, VEN tO GND		-0.3	6	V
Іоит	Maximum Continuous Switch Current			2	Α
PD	Power Dissipation at T _A = 25°C		1.2	W	
T _{STG}	Storage Junction Temperature	-65	150	°C	
T _A	Operating Temperature Range	-40	105	°C	
θја	Thermal Resistance, Junction to Ambier		85	°C/W	
ECD	Flastrostatia Discharge Canability	Human Body Model, JESD22-A114	6		14/
ESD	Electrostatic Discharge Capability	2		kV	

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
VIN	Supply Voltage	1.1	5.5	٧
T _A	Ambient Operating Temperature	-40	+105	°C



ELECTRICAL CHARACTERISTICS

Values are at $V_{IN} = 3.3V$ and $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Units
Basic Ope	eration						
Vin	Supply Voltage			1.1		5.5	V
		EN = Enable, I _{OUT} =0mA, V _{IN} = V _{EN} =		7	70		
IQ	Quiescent Current (1)	EN=Enable, Iout=0mA, VIN=VEN=5.5	5V, Ta=85°C ⁽⁴⁾		12		nA
		EN=Enable, I _{OUT} =0mA, V _{IN} =V _{EN} =5.5V, Ta=105°C (4)			32		
		EN = Disable, I _{OUT} =0mA, V _{IN} =1.1V			5		
		EN = Disable, I _{OUT} =0mA, V _{IN} =1.8V			6		1
		EN = Disable, I _{OUT} =0mA, V _{IN} =3.3V			9	35	nA
I_{SD}	Shut Down Current	EN = Disable, I _{OUT} =0mA, V _{IN} =4.5V			13		
		EN = Disable, I _{OUT} =0mA, V _{IN} =5.5V			28	100	1
		EN = Disable, I _{OUT} =0mA, V _{IN} =5.5V,	Ta=85°C (4)		0.6		
		EN = Disable, I _{OUT} =0mA, V _{IN} =5.5V,	Ta=105°C (4)		2.0		uA
			Ta=25°C		25	30	
Ron	On-Resistance	_	Ta=85°C (4)		30		1
			Ta=105°C (4)		32		1
			Ta=25°C		30	36	
		V _{IN} =3.3V, I _{OUT} = 500mA	Ta=85°C (4)		37		mΩ
		TEGRAT	Ta=105°C (4)		39		2
		V _{IN} =1.8V, I _{OUT} = 300mA	Ta=25°C		46		-
		V _{IN} =1.1V, I _{OUT} = 100mA	Ta=25°C		100		
R _{DSC}	Output Discharge Resistance	E _N =Low, I _{FORCE} = 10mA		70	85	100	Ω
	EN Input Logic High	V _{IN} =1.1V - 1.8V		0.9			V
VIH	Voltage	V _{IN} =1.8V - 5.5V					V
\/	EN Input Logic Low	V _{IN} =1.1V - 1.8V				0.3	V
VIL	Voltage	V _{IN} =1.8V - 5.5V				0.4	V
R _{EN}	EN pull down resistance	Internal Resistance			10		МΩ
I _{EN}	EN Current	E _N =5.5V				1.0	μA
Switching	Characteristics (2, 3, 4)						
t _{dON}	Turn-On Delay	D 4500 0 04v5			1.5		
t _R	V _{OUT} Rise Time	R _L =150Ω, C _{OUT} =0.1μF			2.2		1
t _{dON}	Turn-On Delay	D 5000 0 0 445			1.3		ms
t _R	V _{OUT} Rise Time	R _L =500Ω, C _{OUT} =0.1μF			2.0		1
t _{dOFF}	Turn-Off Delay	R _L =150Ω, C _{OUT} =0.1μF			1.2		
t _F	Vout Fall Time	ΓL=100Ω, COUT=0.1μΓ			14] ,,,
t _{dOFF}	Turn-Off Delay	P5000 Cour-0 145			1.2		us
t _F	V _{OUT} Fall Time	$R_L=500\Omega$, $C_{OUT}=0.1\mu F$			17		

Notes:

- 1. IQ does NOT include Enable pull down current through the pull down resistor RPD.

- t_{ON} = t_{dON} + t_R, t_{OFF} = t_{dOFF} + t_F
 Output discharge path is enabled during off.
 By design; characterized, not production tested



TIMING DIAGRAM

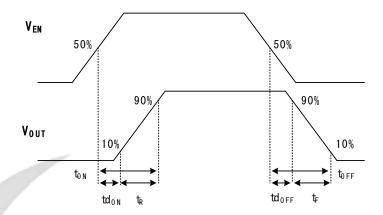


Figure 2. Timing Diagram





TYPICAL PERFORMANCE CHARACTERISTICS

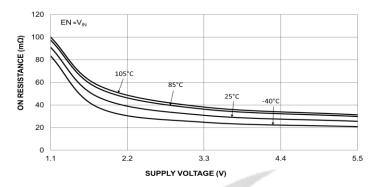


Figure 3. On-Resistance vs. Supply Voltage

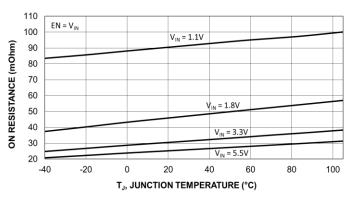


Figure 4. On-Resistance vs. Temperature

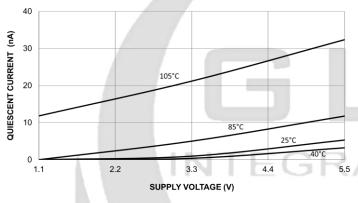


Figure 5. Quiescent Current vs. Supply Voltage

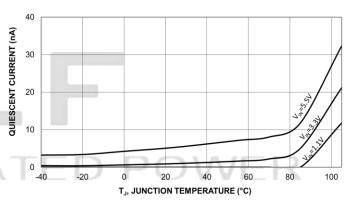


Figure 6. Quiescent Current vs. Temperature

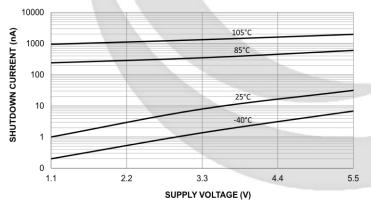


Figure 7. Shutdown Current vs. Input Voltage

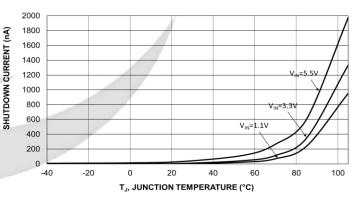


Figure 8. Shutdown Current vs. Temperature

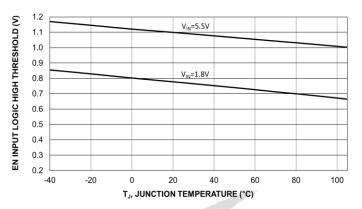


Figure 9. EN Input Logic High Threshold Vs. Temperature

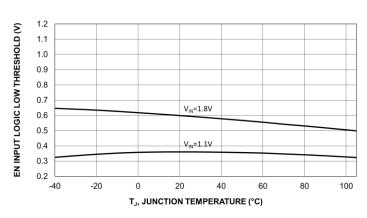


Figure 10. EN Input Logic Low Threshold Vs. Temperature

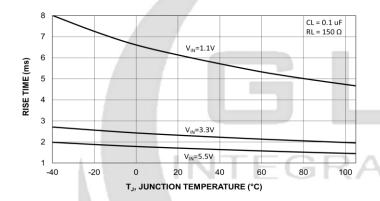


Figure 11. Vout Rise Time vs. Temperature

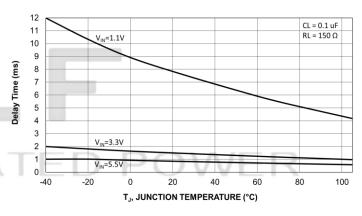


Figure 122. Turn-On Delay Time vs. Temperature

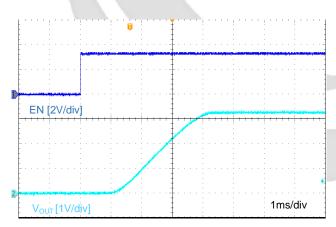


Figure 133. Turn-On Response $V_{\text{IN}=3.3} \text{ V, C}_{\text{IN}=1.0} \text{ uF, C}_{\text{OUT}=0.1} \text{ uF, R}_{\text{L}=150} \ \Omega$

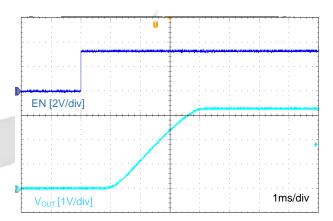


Figure 144. Turn-On Response $\label{eq:Vin=3.3} V, C_{\text{IN}=1.0} \text{ uF, } C_{\text{OUT}=0.1} \text{ uF, } R_{\text{L}=500} \text{ } \Omega$

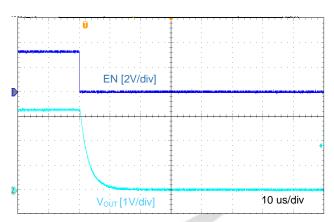


Figure 155. Turn-Off Response, Output Discharge V_{IN} =3.3 V, C_{IN} =1.0 uF, C_{OUT} =0.1 uF, R_L =150 Ω

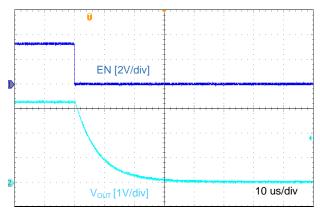


Figure 6. Turn-Off Response, Output Discharge V_{IN}=3.3 V, C_{IN}=1.0 uF, C_{OUT}=0.1 uF, R_L=500 Ω





Nano-Current Consumed, I_QSmart[™] Load Switch

APPLICATION INFORMATION

The GLF71511 integrated 2A, Ultra-Efficient I_QSmartTM Load Switch devices with a fixed slew rate control to limit the inrush current during turn on. Each device is capable of operating over a wide input range from 1.1 V to 5.5 V with very low on-resistance to reduce conduction loss. In the off state, these devices consume very low leakage current to avoid unwanted standby current and save limited input power. The package is a 0.97 mm x 0.97 mm x 0.55 mm wafer level chip scale package, saving space in compact applications. It is constructed using 4 bumps, with a 0.5 mm pitch for manufacturability.

Input Capacitor

The GLF71511 does not require an input capacitor. However, to reduce the voltage drop on the input power rail caused by transient inrush current at start-up, a 0.1uF capacitor is recommended to be placed close to the V_{IN} pin. A higher input capacitor value can be used to further attenuate the input voltage drop.

Output Capacitor

The GLF71511 does not require an output capacitor. However, use of an output capacitor is recommended to mitigate voltage undershoot on the output pin when the switch is turning off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The C_{OUT} capacitor should be spaced close to the VOUT and GND pins.

EN pin

The GLF71511 can be activated by forcing EN pin high level. Note that the EN pin has an internal pull-down resistor to help pull the main switch to a known "off state" when no EN signal is applied from an external controller.

Output Discharge Function

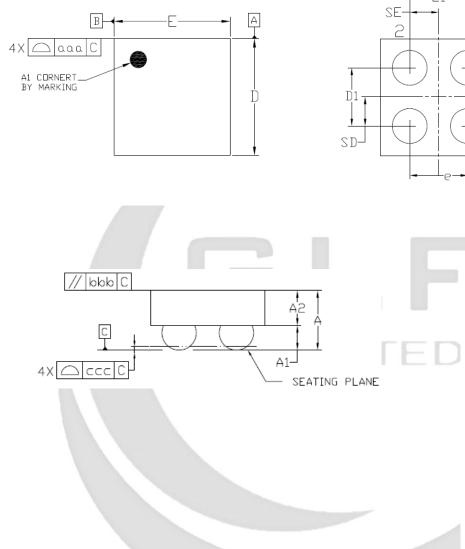
The GLF71511 has an internal discharge N-channel FET switch on the VOUT pin. When EN signal turns the main power FET to an off state, the N-channel switch turns on to discharge an output capacitor quickly.

Board Layout

All traces should be as short as possible to minimize parasitic inductance effects. Wide traces for VIN, VOUT, and GND will help reduce signal degradation and parasitic effects during dynamic operation as well as improve the thermal performance at high load current.



PACKAGE OUTLINE



Dimensional Ref.								
REF.	Min.	Nom.	Max.					
Α	0.500	0.550	0.600					
Α1	0.225	0.250	0.275					
A2	0.275	0.300	0.325					
D	0.955	0.970	0.985					
Е	0.955	0.970	0.985					
D1	0.450	0.500	0.550					
E1	0.450	0.500	0.550					
Ь	0.260	0.310	0.360					
е	0	.500 BS	C					
SD	0	.250 BS	C					
SE	0	.250 BS	C					
To	ol. of Fo	rm&Po:	sition					
999	0.10							
ььь	0.10							
CCC	0.05							
ddd		0.05						

4X Øb

◆ ØdddM C B A

<u>Notes</u>

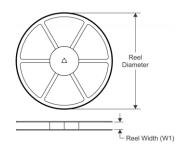
- 1. ALL DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
- 2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.

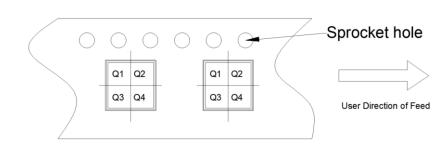


TAPE AND REEL INFORMATION

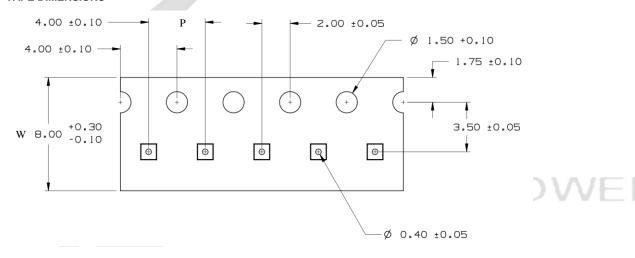
REEL DIMENSIONS

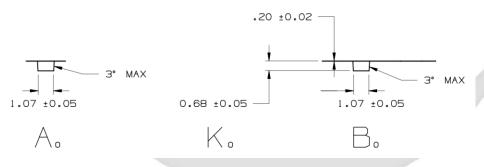
QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE





TAPE DIMENSIONS





-	Device	Package	Pins	SPQ	Reel Diameter(mm)	Reel Width W1	Α0	В0	КО	Р	w	Pin1
G	LF71511	WLCSP	4	3000	180	9	1.07	1.07	0.68	4	8	Q1

Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P: Pitch between successive cavity centers



Nano-Current Consumed, I_QSmart[™] Load Switch

SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	' I chande the checitication at any time without warning or notification a li	
Product Specification	Product This document represents the anticipated production performance	

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